SIEMENS

Preliminary Datasheet

SFH 48 0442
SFH 48 0443

InGaAs - Laser Diode 1000 mW

Wavelength 940 nm, chip on carrier

Data differing from SFH 48 0402 and SFH 48 0403:

Characteristic Data: Parameter:	**Typical Values**		**Unit**	**Condition**
Lambda	940 +/- 10		nm	DC, 1W
FWHM	4		nm	
Ith	450		mA	
eta	0,8		W/A	in NA=0,6
Iop(1W)	1700	<2000	mA	in NA=0,6
Uop(1W)	2100	<2500	mV	
Rs	2100	<0,5	Ohm	
TCLambda	0,3	0,35	nm/K	temperature coefficient of wavelength
TCI	1		%/K	temperature coefficient of operation current

Maximum Ratings:			
cw-output power	1050	mW	
operating temperature	-10 ... +40°C	°C	bedewing is excluded
reverse voltage	1	V	